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Characterization of Irradiated Silicon Sensors for HGAL
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As part of High Luminosity LHC (HL-LHC) project, the high-granularity calorimeter (HGAL) will be a major upgrade of CMS experiment to replace the current endcap calorimeter. Due to the higher instantaneous luminosity of the HL-LHC and the rapidity range the HGAL will cover, radiation tolerance is a primary design consideration. The majority of the HGAL will be based on 120-, 200-, and 300 μm thick silicon (Si) pad sensors and will sustain 1-MeV neutron equivalent fluences up to about $10^{16} \text{ neqcm}^{-2}$. Campaigns have been underway to determine the level of degradation expected over the full life of the detector. A first study of irradiated test diode samples from 8-inch and 6-inch wafers at -30 C is presented, including all three thicknesses and both bulk polarities. The electrical and charge collection properties are characterized after irradiation by current-voltage, capacitance-voltage and infrared Transient Current Technique measurements for sensors exposed to various fluence levels.

¹The Compact Muon Solenoid (CMS) experiment at CERN

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